

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(annealing AND semiconductor AND structure AND diffuse AND contaminants AND surface AND particulate AND semiconductor AND material AND after AND annealing AND semiconductor AND structure AND exposing AND surface AND semiconductor AND structure AND vicinity AND surface AND particulate AND high AND intensity AND beam AND light AND suitable AND light AND source).CLM.	US-PGPUB	OR	ON	2009/04/30 10:52
L2	5659	(356/237.1-237.5).OCLS.	US-PGPUB; USPAT; USOCR; EPO	OR	OFF	2009/04/30 10:55
L3	23	2 and ((detect\$3 inspect\$3) same (intensity photoluminescence excitation contamination contaminant) same anneal\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2009/04/30 10:56
L4	17	(HIGGS near VICTOR).in.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2009/04/30 11:09
L5	1	3 and L4	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2009/04/30 11:09
S1	10	((("0229883") or ("2077621")). PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2008/04/13 15:00
S2	16	(HIGGS near VICTOR).in.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/13 15:04
S3	0	S2 and ((detect\$3 inspect\$3) same (expos\$4) same (dark \$1field darkfield\$1 bright \$1field brightfield) same (compar\$3 measur\$3 determ \$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant) same (particulate particle\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/13 15:56

S4	1	((detect\$3 inspect\$3) same (expos\$4) same (dark\$1field darkfield\$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant) same (particulate particle\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/13 15:57
S5	0	S2 and ((detect\$3 inspect\$3) same (expos\$4) same (dark\$1field darkfield\$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/13 15:58
S6	6	S2 and ((detect\$3 inspect\$3) same (expos\$4 dark\$1field darkfield\$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/13 15:59
S7	4	("20020109110" "5943552" "6159859").PN. OR ("6911347").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/04/13 16:08
S8	1	("20040106217").PN.	US-PGPUB; USPAT; USOCR; EPO	OR	OFF	2008/04/13 16:11
S9	1	S8 and ((detect\$3 inspect\$3) same (expos\$4 dark\$1field darkfield\$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/13 16:11
S10	863	((detect\$3 inspect\$3) same (expos\$4 dark\$1field darkfield\$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant) same metal)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/13 16:12
S11	36	S10 and ((356/???".cds")	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/13 16:13

S12	45	S10 and ((356/???.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/13 16:13
S13	863	((detect\$3 inspect\$3) same (expos\$4 dark\$1field darkfield \$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant) same metal)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/22 14:24
S14	36	S13 and ((356/???.ccls")	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/22 14:24
S15	45	S13 and ((356/???.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/22 14:24
S16	0	S14 and S15 and (photoluminescence)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/22 14:24
S17	5	S14 and S15 and (photoluminescence Photo \$1luminescence luminescence)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/22 14:25
S18	57	S13 and (photoluminescence Photo\$1luminescence luminescence)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/04/22 14:28
S19	867	((detect\$3 inspect\$3) same (expos\$4 dark\$1field darkfield \$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant) same metal)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/05/12 10:45
S20	58	S19 and (photoluminescence Photo\$1luminescence luminescence)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/05/12 10:45
S21	2	S20 and ((compar\$3 detect\$3 inspect\$3) same (defect\$1 flaw \$1 contaminat\$3) same (photoluminescence Photo \$1luminescence luminescence) same diffus\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/05/12 10:45

S22	16	((compar\$3 detect\$3 inspect\$3) same (defect\$1 flaw\$1 contaminat\$3) same (photoluminescence Photo\$1luminescence luminescence) same diffus\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/05/12 10:46
S23	1	(comparator AND compare AND photoluminescence AND responses AND determine AND difference AND diffusion AND identify AND contaminant).CLM.	US-PGPUB	OR	ON	2008/05/12 10:58
S24	868	((detect\$3 inspect\$3) same (expos\$4 dark\$1field darkfield\$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant) same metal)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/05/13 11:20
S25	58	S24 and (photoluminescence Photo\$1luminescence luminescence)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/05/13 11:20
S26	1	S25 and (heat\$2 near\$3 stage)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/05/13 11:20
S27	6	S24 and (heat\$2 near\$3 stage)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/05/13 11:21
S28	440	((anneal\$3 diffus\$3) adj\$3 (contaminant\$1 substanc\$2) adj\$3 (substrate structure material))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 12:34
S29	2	S28 and (heat\$2 near\$3 stage)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 12:35
S30	11	S28 and (heat\$2 near\$3 (table holder stage))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 12:39
S31	717	((anneal\$3 diffus\$3 dop\$3) adj\$3 (contaminant\$1 substanc\$2) adj\$3 (substrate structure material semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 12:43
S32	16	S31 and (heat\$2 near\$3 (table holder stage))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 12:44

S33	1	("20040252297").FN.	US-PGPUB; USPAT; USOCR; EPO	OR	OFF	2008/11/22 13:45
S34	0	S33 and (heat\$2 near\$3 (table holder stage))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 13:46
S35	0	S34 and ((anneal\$3 diffus\$3 dop\$3) adj3 (contaminant\$1 substanc\$2) adj3 (substrate structure material semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 13:46
S36	0	S33 and ((detect\$3 inspect\$3) same (expos\$4 dark\$1field darkfield\$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant) same metal)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 13:47
S37	0	S33 and (photoluminescence Photo\$1luminescence luminescence)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 13:47
S38	1	S33 and ((detect\$3 inspect\$3) same (expos\$4 dark\$1field darkfield\$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) (intensity photoluminescence excitation contamination contaminant) same metal)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 13:47
S39	94748	((heat\$2 mean\$1) adj5 (table holder stage sample))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 15:22
S40	13	S39 and ((anneal\$3 diffus\$3 dop\$3) adj3 (contaminant\$1 substanc\$2) adj3 (substrate structure material semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 15:22
S41	27645	S39 and ((anneal\$3 diffus\$3 dop\$3) (contaminant\$1 substanc\$2) adj3 (substrate structure material semiconductor))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 15:44
S42	1072	S41 and ((356/ ???".ccls")	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 15:44

S43	0	S42 and ((compar\$3 detect\$3 inspect\$3) same (defect\$1 flaw\$1 contaminat\$3) same (photoluminescence Photo\$1luminescence luminescence) same diffus\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 15:45
S44	29	S42 and ((detect\$3 inspect\$3) same (expos\$4 dark\$1field darkfield\$1 bright\$1field brightfield) same (compar\$3 measur\$3 determ\$5 calculat\$3 identif\$4) same (intensity photoluminescence excitation contamination contaminant))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 15:45
S45	10	S44 and (@py<"2004")	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 15:46
S46	5154	S41 and (heat\$2 near\$3 stage)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 15:54
S47	3205	S46 and (@py<"2004")	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 15:54
S48	42	S47 and (((356/???)."cds")	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2008/11/22 15:55
S49	2562	(anneal\$3 near10 semiconductor near10 diffus\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/28 09:46
S50	677516	defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/28 09:46
S51	128	S49 same S50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/28 09:48
S52	128	S51 and (@py<"20030409")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/28 09:48

S53	75	S51 and (@ad<"20030409")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/28 09:49
S54	0	S51 and ((@ad<"20030409") same metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/28 10:06
S55	40	S53 and (metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/28 10:07

4/ 30/ 2009 11:10:10 AM

C:\ Documents and Settings\ iakanbi\ My Documents\ EAST\ Workspaces\ 10549865.wsp